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# SIDC03D60F6

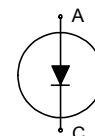
## Fast switching diode

### Features:

- 600V Emitter Controlled technology 70  $\mu\text{m}$  chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

### This chip is used for:

- power modules and discrete devices



### Applications:

- SMPS, resonant applications, drives

Chip Type	$V_R$	$I_F$	Die Size	Package
SIDC03D60F6	600V	6A	1.2 x 2.25 mm <sup>2</sup>	sawn on foil

### Mechanical Parameters

Raster size	1.2 x 2.25	mm <sup>2</sup>
Area total	2.7	
Anode pad size	0.718 x 1.768	
Thickness	70	$\mu\text{m}$
Wafer size	150	mm
Max. possible chips per wafer	5650	
Passivation frontside	Photoimide	
Pad metal	3200 nm AlSiCu	
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, $\leq 250\mu\text{m}$	
Reject ink dot size	$\varnothing 0.65\text{mm}$ ; max 1.2mm	
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C	



# SIDC03D60F6

## Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25\text{ °C}$	600	V
Continuous forward current	$I_F$	$T_{vj} < 150\text{ °C}$	<sup>1)</sup>	A
Maximum repetitive forward current	$I_{FRM}$	$T_{vj} < 150\text{ °C}$	12	
Junction temperature range	$T_{vj}$		-40...+175	°C
Operating junction temperature	$T_{vj}$		-40...+150	°C
Dynamic ruggedness <sup>2)</sup>	$P_{max}$	$I_{Fmax} = 12A, V_{Rmax} = 600V,$ $T_{vj} \leq 150\text{ °C}$	tbd	kW

<sup>1)</sup> depending on thermal properties of assembly

<sup>2)</sup> not subject to production test - verified by design/characterisation

## Static Characteristic (tested on wafer), $T_{vj} = 25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse leakage current	$I_R$	$V_R = 600V$			27	$\mu A$
Cathode-Anode breakdown Voltage	$V_{BR}$	$I_R = 0.5mA$	600			V
Diode forward voltage	$V_F$	$I_F = 6A$		1.6		V

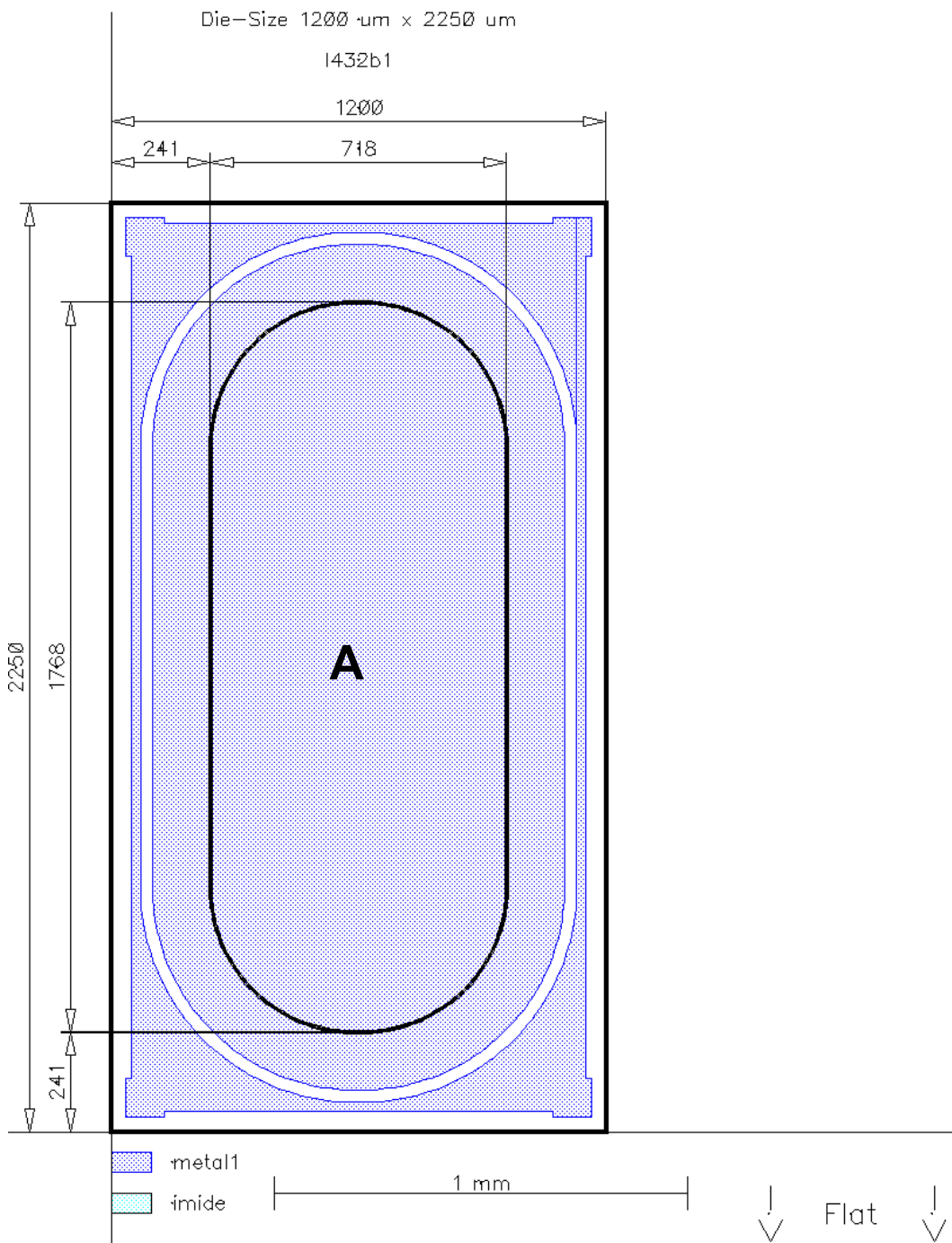
## Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.



# SIDC03D60F6

## Chip Drawing



**A: Anode pad**



# SIDC03D60F6

## Description

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

## Revision History

Version	Subjects (major changes since last revision)	Date

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